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(71) Applicant (for all designated States except US): NANYANG TECHNOLOGICAL UNIVERSITY [SG/SG]; Nanyang Avenue, Singapore 639798 (SG).

(72) Inventors; and

(75) Inventors/Applicants (for US only): SHI, Xu [SG/SG]; BLK 356 #02-402, Woodlands Avenue 5, Singapore 730356 (SG). TAY, Beng, Kang [SG/SG]; 18 Sin Ming Walk #06-01, Singapore 575569 (SG). TAN, Hong, Siang [MY/MY]; 24 Jalan 17/1, 46400 Petaling Jaya, Selangor (MY). FLYNN, David, Ian [GB/SG]; BLK 726 #08-244, Gek Poh Ville, Singapore 640726 (SG).

(74) Agent: SCHLICH, George, William; Mathys & Squire, 100 Gray's Inn Road, London WC1X 8AL (GB).

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(54) Title: CATHODE ARC SOURCE AND GRAPHITE TARGET

(57) Abstract

A cathode arc source has means for generating first and second magnetic fields, of opposite or reverse direction to each other. The resultant magnetic field includes a null point between the target and the substrate, though close to the target. Field strength normal to the target is zero at the null point, and field strength lateral to the target is strong at the null point. A target is made by pressing graphite powder at elevated temperature and pressure in the absence of binding material. Both source and target contribute to reduced macroparticles in deposited films.

